

# **2011 International Conference on Simulation of Semiconductor Processes and Devices**

**(SISPAD 2011)**

**Osaka, Japan  
8 – 10 September 2011**



**IEEE Catalog Number: CFP11SSD-PRT  
ISBN: 978-1-61284-419-0**

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N. Goldsman, *Univ. Maryland, USA*

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## Saturday, September 10

### Session 8: Compact Model (Ginga)

Chairpersons: T. Tanaka, *Fujitsu Semiconductor, Japan*  
A. Heringa, *NXP Semiconductors, Netherland*

- 9:20 **(Invited) A Spice-based Multi-physics Simulation Technique for Integrated MEMS**  
**8-1** H. Toshiyoshi  
*Univ. Tokyo, Japan* ..... 239
- 9:50 Coffee Break**
- 10:10 **2D Analytical Model for the Study of NEM Relay Device Scaling**  
**8-2** X. Shen, S. Chong, D. Lee, R. Parsa, R. T. Howe and H.-S. P. Wong  
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- 10:30 **Accurate and global model of SOI H gate body-tied MOSFET for circuit simulator**  
**8-3** M. Mochizuki<sup>1</sup>, H. Hayashi<sup>1</sup>, S. Ishii<sup>1</sup>, S. Ohira<sup>1</sup>, I. Kurachi<sup>1</sup> and N. Miura<sup>2</sup>  
<sup>1</sup>*Oki Semiconductor Co., Ltd., Japan* and <sup>2</sup>*Oki Semiconductor Miyagi Co., Ltd., Japan* ..... 247
- 10:50 **Modeling Temperature and Bias Stress Effect on Threshold Voltage of a-Si:H TFTs for Gate Driver Circuit Simulation**  
**8-4** C.-H. Shen, Y. Li, I.-H. Lo, P.-J. Lin and S.-C. Chung  
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- 11:10 **Characterization and Modeling of Self-Heating Effect on Transient Current Overshoot in Poly-Si TFTs Fabricated on Glass Substrate**  
**8-5** T. Ota<sup>1</sup>, H. Tsuji<sup>1,2</sup>, Y. Kamakura<sup>1</sup> and K. Taniguchi<sup>1</sup>  
<sup>1</sup>*Osaka Univ., Japan* and <sup>2</sup>*CREST, Japan* ..... 255

### Session 9: Tunneling (Izumi)

Chairpersons: K. Fukuda, *AIST, Japan*  
T. Grasser, *TU Wien, Austria*

- 10:10 **3D Modeling based on Current Continuity for STM Carrier Profiling of Semiconductor Devices**  
**9-1** K. Fukuda<sup>1</sup>, M. Nishizawa<sup>1</sup>, T. Tada<sup>1</sup>, L. Bolotov<sup>2</sup>, K. Suzuki<sup>3</sup>, S. Sato<sup>3</sup>, H. Arimoto<sup>1</sup> and T. Kanayama<sup>1</sup>  
<sup>1</sup>*NIRC AIST, Japan*, <sup>2</sup>*Tsukuba Univ., Japan* and <sup>3</sup>*Fujitsu Semiconductor Ltd., Japan* ..... 259

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	<sup>1</sup> ETH Zürich, Switzerland, <sup>2</sup> Purdue Univ., USA and <sup>3</sup> IBM Research-Zurich, Switzerland .....	263
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	W. G. Vandenberghe <sup>1,2</sup> , B. Sorée <sup>1,2</sup> , W. Magnus <sup>1,3</sup> , G. Groeseneken <sup>1,2</sup> , A. S. Verhulst <sup>1</sup> and M. V. Fischetti <sup>4</sup>	
	<sup>1</sup> imec, Belgium, <sup>2</sup> Katholieke Univ. Leuven, Belgium, <sup>3</sup> Univ. Antwerpen, Belgium and <sup>4</sup> Univ. Texas Dallas, USA .....	271
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A. Martinez, <i>Univ. Glasgow, UK</i>		
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10-1	C.L. Alexander <sup>1</sup> and Asen Asenov <sup>1,2</sup>	
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10-2	S. M. Amoroso <sup>1</sup> , C. L. Alexander <sup>2</sup> , S. Markov <sup>2</sup> , G. Roy <sup>3</sup> and A. Asenov <sup>2,3</sup>	
	<sup>1</sup> Politecnico di Milano-IU.NET, Italy, <sup>2</sup> Univ. Glasgow, UK and <sup>3</sup> Gold Standard Simulations Ltd., UK .....	279
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10-3	P. Asenov <sup>1</sup> , F. Adamu-Lema <sup>1</sup> , S. Roy <sup>1</sup> , C. Millar <sup>1,2</sup> , A. Asenov <sup>1,2</sup> , G. Roy <sup>2</sup> , U. Kovac <sup>2</sup> and D. Reid <sup>2</sup>	
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P. Oldiges, <i>IBM, USA</i>		
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<b>11-1</b>	V. Peikert and A. Schenk	
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